



AF
2800
BOX AF

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

INOUE et al.

Serial Number: **09/473,988**

19/D
4-26-02
Group Art Unit: 2814

Filed: **December 29, 1999**

Examiner: **T. Doan**

For: **SEMICONDUCTOR DEVICE AND METHOD OF MANUFACTURING THE SAME**

RECEIVED
APR 24 2002
TECHNOLOGY CENTER 2800

AMENDMENT AFTER FINAL REJECTION

BOX AF

Commissioner for Patents
Washington, D.C. 20231

April 22, 2002

Sir:

In response to the Office Action dated January 25, 2002, please amend the above-identified application as follows:

IN THE CLAIMS:

Please amend claims 1, 2 and 7-9 as follows:

1. (Four Times Amended) A semiconductor device comprising an insulating interlayer formed on a conductive film, said insulating interlayer including:
a first insulating layer of a composition containing SiH;
a second insulating layer formed on said first insulating layer; and
a third insulating layer formed between said conductive film and said first insulating layer,